

TO-92 Plastic-Encapsulate Transistors

2N5401 TRANSISTOR (PNP)

FEATURES

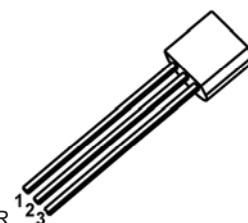
- Switching and Amplification in High Voltage
- Applications such as Telephony
- Low Current
- High Voltage

TO - 92

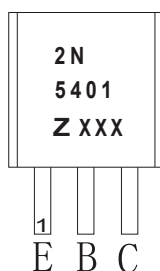
1. EMITTER

2. BASE

3. COLLECTOR



MARKING



2N5401=Device code

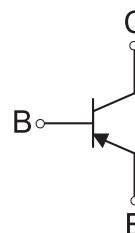
Z=Rank of h_{FE}

XXX=Code

GXX=Green molding compound device

CXX=Normal molding compound device

Equivalent Circuit



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2N5401	TO-92	Bulk	1000pcs/Bag
2N5401-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS ($T_a=25\text{ }^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.6	A
P_C	Collector Power Dissipation	625	mW
R_{KJA}	Thermal Resistance From Junction To Ambient	200	$^{\circ}\text{C} / \text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS

$T_a=25^{\circ}\text{C}$ unless otherwise specified

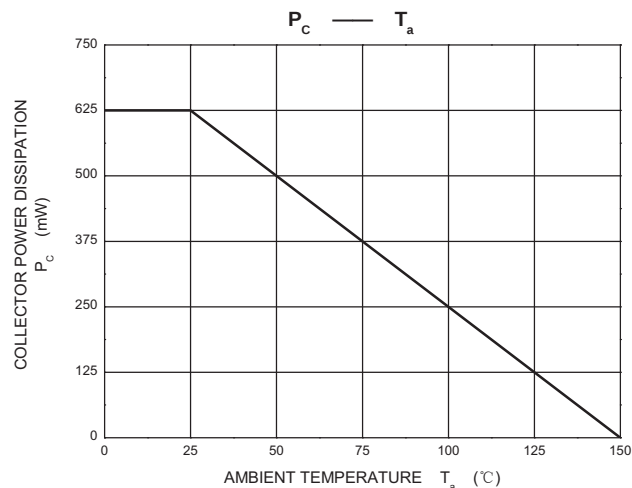
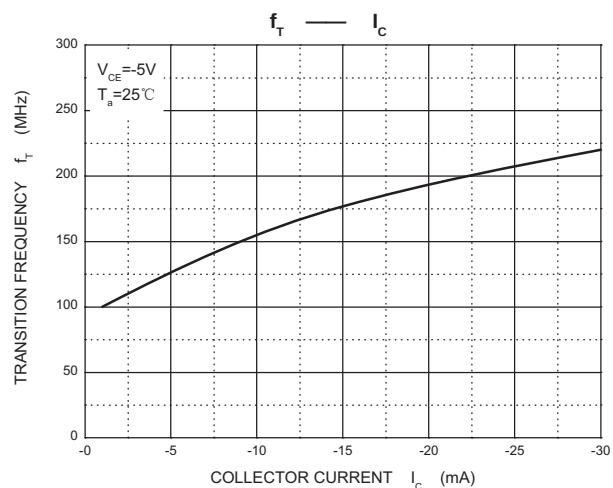
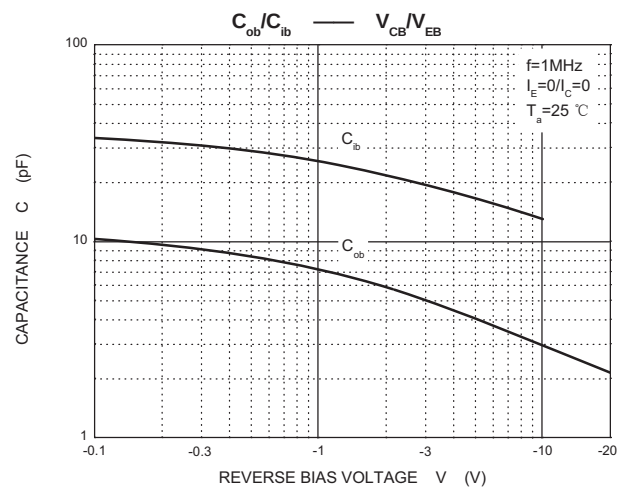
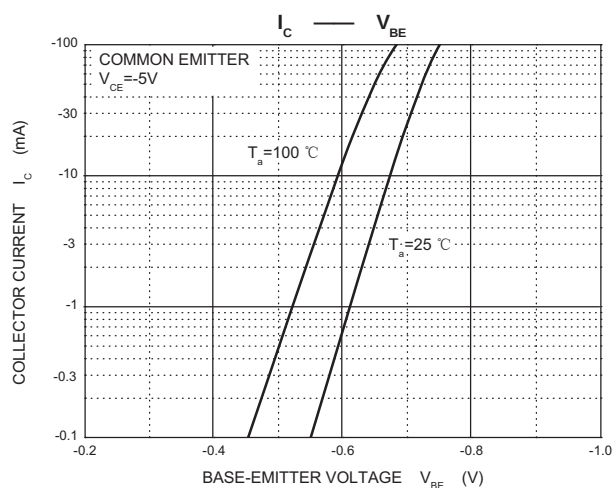
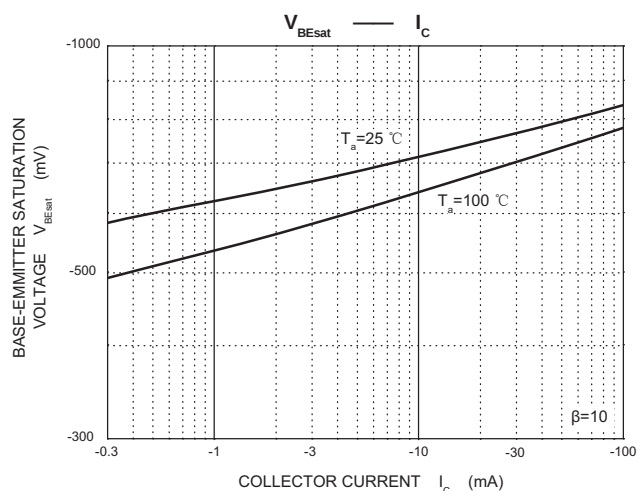
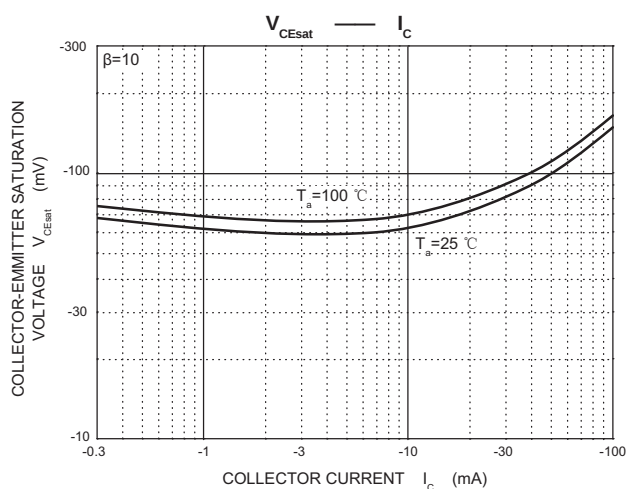
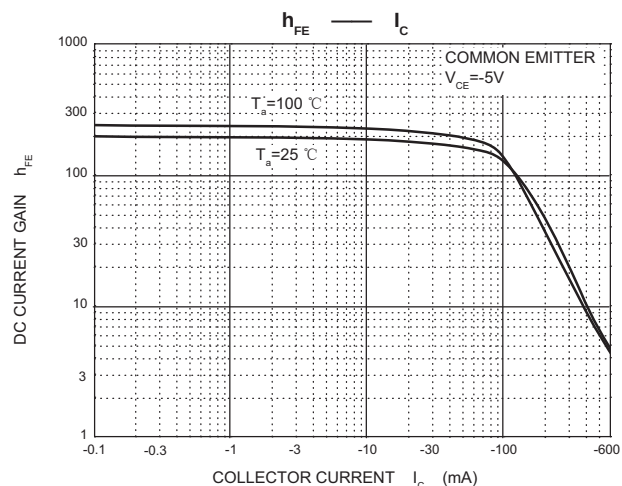
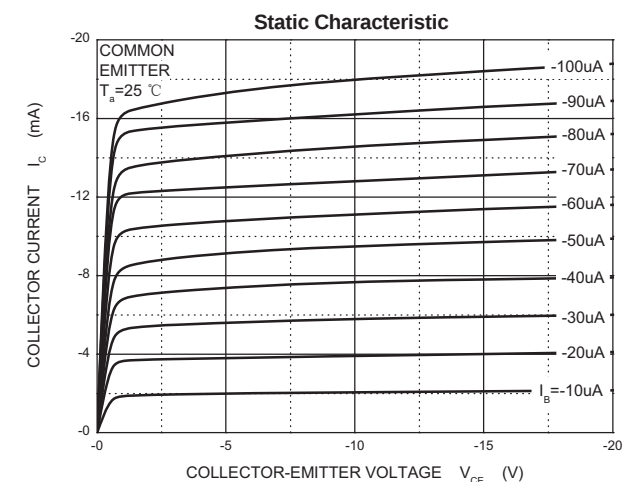
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1\text{mA}, I_E = 0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.01\text{mA}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -120\text{V}, I_E = 0$			-50	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3\text{V}, I_C = 0$			-50	nA
DC current gain	$h_{FE(1)}$	$V_{CE} = -5\text{V}, I_C = -1\text{mA}$	80			
	$h_{FE(2)}$	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$	100		300	
	$h_{FE(3)}$	$V_{CE} = -5\text{V}, I_C = -50\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}, f = 30\text{MHz}$	100		300	MHz

*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2.0\%$.

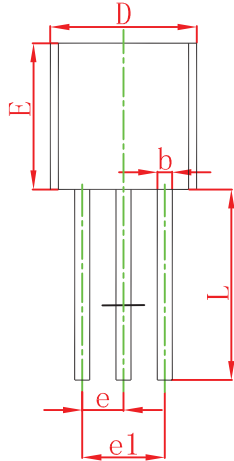
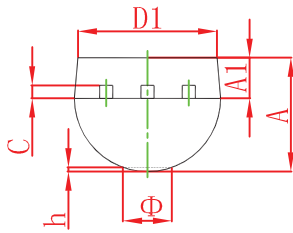
CLASSIFICATION OF $h_{FE(2)}$

RANK	A	B	C
RANGE	100-150	150-200	200-300

Typical Characteristics

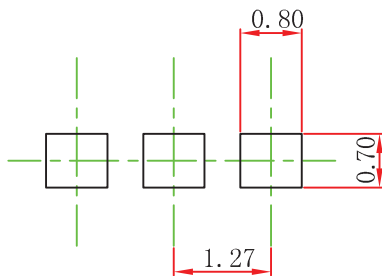


TO-92 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015

TO-92 Suggested Pad Layout

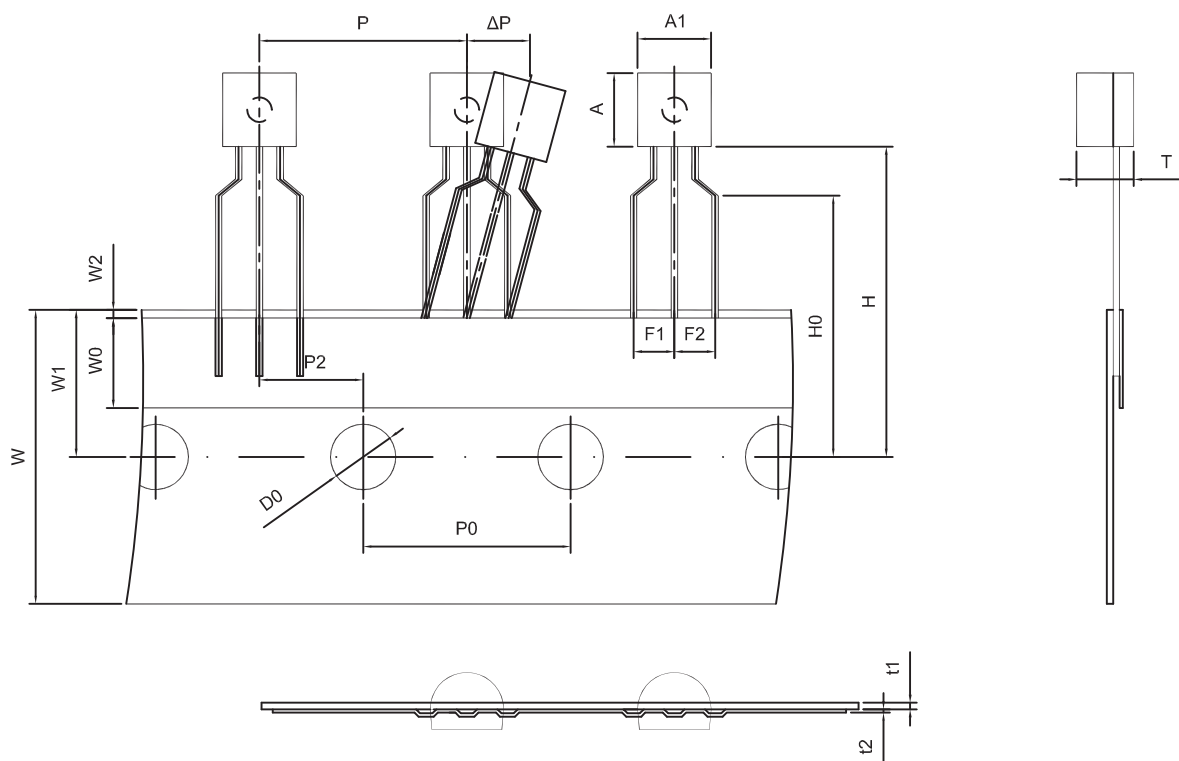


Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

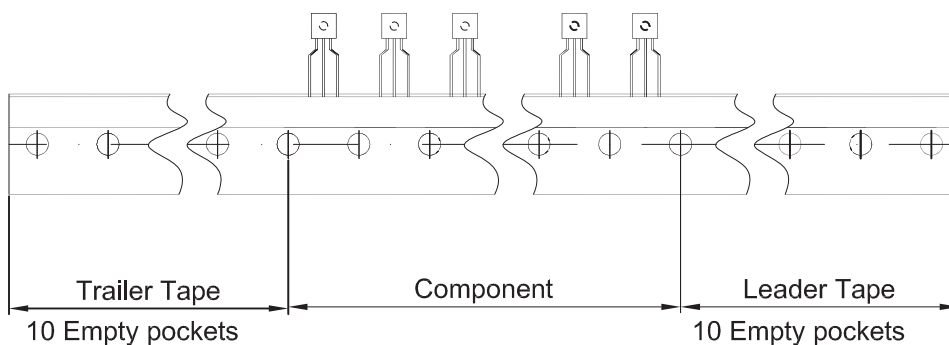
NOTICE

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Dimiensions are in millimeter

A1	A	T	P	P0	P2	F1	F2	W
4.5	4.5	3.5	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	H	H0	D0	t1	t2	ΔP
6.0	9.0	1.0 MAX.	19.0	16.0	4.0	0.4	0.2	0



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250